

N-channel 600 V, 0.195 Ω typ., 15 A MDmesh™ DM2 Power MOSFET in a PowerFLAT™ 8x8 HV package

Datasheet - production data

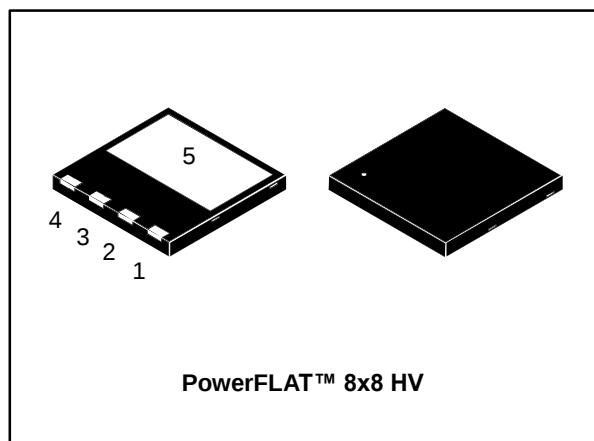
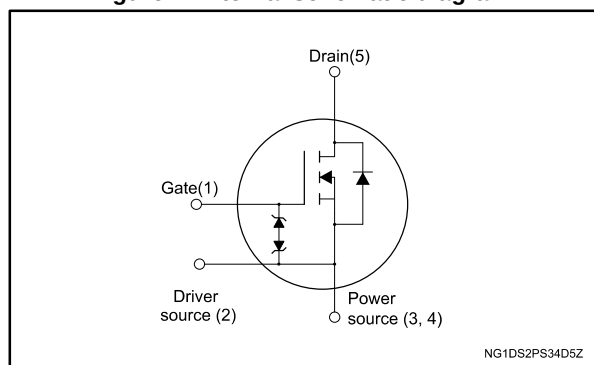


Figure 1: Internal schematic diagram



Features

Order code	V _{DS} @ T _{Jmax}	R _{DS(on)} max.	I _D
STL24N60DM2	650 V	0.220 Ω	15 A

- Fast-recovery body diode
- Extremely low gate charge and input capacitance
- Low on-resistance
- 100% avalanche tested
- Extremely high dv/dt ruggedness
- Zener-protected

Applications

- Switching applications

Description

This high voltage N-channel Power MOSFET is part of the MDmesh™ DM2 fast recovery diode series. It offers very low recovery charge (Q_{rr}) and time (t_{rr}) combined with low $R_{DS(on)}$, rendering it suitable for the most demanding high efficiency converters and ideal for bridge topologies and ZVS phase-shift converters.

Table 1: Device summary

Order code	Marking	Package	Packing
STL24N60DM2	24N60DM2	PowerFLAT™ 8x8 HV	Tape and reel

Contents

1	Electrical ratings	3
2	Electrical characteristics	4
	2.1 Electrical characteristics (curves).....	6
3	Test circuits	8
4	Package information	9
	4.1 PowerFLAT8x8 HV package information	10
	4.2 PowerFLAT8x8 HV packaging information	12
5	Revision history	14

1 Electrical ratings

Table 2: Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{GS}	Gate-source voltage	± 25	V
$I_D^{(1)}$	Drain current (continuous) at $T_{case} = 25\text{ }^{\circ}\text{C}$	15	A
	Drain current (continuous) at $T_{case} = 100\text{ }^{\circ}\text{C}$	9.5	
$I_{DM}^{(1)(2)}$	Drain current (pulsed)	60	A
$P_{TOT}^{(1)}$	Total dissipation at $T_{case} = 25\text{ }^{\circ}\text{C}$	125	W
$dv/dt^{(3)}$	Peak diode recovery voltage slope	40	V/ns
$dv/dt^{(4)}$	MOSFET dv/dt ruggedness	50	
T_{stg}	Storage temperature range	-55 to 150	$^{\circ}\text{C}$
T_j	Operating junction temperature range		

Notes:

⁽¹⁾The value is limited by package

⁽²⁾Pulse width limited by safe operating area.

⁽³⁾ $I_{SD} \leq 15\text{ A}$, $di/dt \leq 400\text{ A}/\mu\text{s}$, $V_{DS(peak)} < V_{(BR)DSS}$, $V_{DD}=400\text{ V}$

⁽⁴⁾ $V_{DS} \leq 480\text{ V}$.

Table 3: Thermal data

Symbol	Parameter	Value	Unit
$R_{thj-case}$	Thermal resistance junction-case	1	$^{\circ}\text{C}/\text{W}$
$R_{thj-pcb}^{(1)}$	Thermal resistance junction-pcb	45	

Notes:

⁽¹⁾When mounted on FR-4 board of inch^2 , 2oz Cu.

Table 4: Avalanche characteristics

Symbol	Parameter	Value	Unit
I_{AR}	Avalanche current, repetitive or not repetitive (pulse width limited by T_{Jmax})	3	A
E_{AS}	Single pulse avalanche energy (starting $T_j = 25\text{ }^{\circ}\text{C}$, $I_D = I_{AR}$, $V_{DD} = 50\text{ V}$)	160	mJ

2 Electrical characteristics

(T_{case} = 25 °C unless otherwise specified)

Table 5: On/off-state

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
V _{(BR)DSS}	Drain-source breakdown voltage	V _{GS} = 0 V, I _D = 1 mA	600			V
I _{DSS}	Zero gate voltage drain current	V _{GS} = 0 V, V _{DS} = 600 V			1.5	μA
		V _{GS} = 0 V, V _{DS} = 600 V, T _{case} = 125 °C			100	
I _{GSS}	Gate-body leakage current	V _{DS} = 0 V, V _{GS} = ±25 V			±10	μA
V _{GS(th)}	Gate threshold voltage	V _{DS} = V _{GS} , I _D = 250 μA	3	4	5	V
R _{DS(on)}	Static drain-source on-resistance	V _{GS} = 10 V, I _D = 9 A		0.195	0.220	Ω

Table 6: Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C _{iss}	Input capacitance	V _{DS} = 100 V, f = 1 MHz, V _{GS} = 0 V	-	1055	-	pF
C _{oss}	Output capacitance		-	56	-	
C _{rss}	Reverse transfer capacitance		-	2.4	-	
C _{oss eq.} ⁽¹⁾	Equivalent output capacitance	V _{DS} = 0 to 480 V, V _{GS} = 0 V	-	259	-	pF
R _G	Intrinsic gate resistance	f = 1 MHz, I _D = 0 A	-	7	-	Ω
Q _g	Total gate charge	V _{DD} = 480 V, I _D = 18 A, V _{GS} = 10 V (see Figure 15: "Gate charge test circuit")	-	29	-	nC
Q _{gs}	Gate-source charge		-	6	-	
Q _{gd}	Gate-drain charge		-	12	-	

Notes:

⁽¹⁾ C_{oss eq.} is defined as a constant equivalent capacitance giving the same charging time as C_{oss} when V_{DS} increases from 0 to 80% V_{DSS}.

Table 7: Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
t _{d(on)}	Turn-on delay time	V _{DD} = 300 V, I _D = 9 A, R _G = 4.7 Ω, V _{GS} = 10 V (see Figure 14: "Switching times test circuit for resistive load" and Figure 19: "Switching time waveform")	-	15	-	ns
t _r	Rise time		-	8.7	-	
t _{d(off)}	Turn-off delay time		-	60	-	
t _f	Fall time		-	15	-	

Table 8: Source-drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$I_{SD}^{(1)}$	Source-drain current		-		15	A
$I_{SDM}^{(2)}$	Source-drain current (pulsed)		-		60	A
$V_{SD}^{(3)}$	Forward on voltage	$V_{GS} = 0\text{ V}$, $I_{SD} = 18\text{ A}$	-		1.6	V
t_{rr}	Reverse recovery time	$I_{SD} = 18\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$, $V_{DD} = 60\text{ V}$ (see Figure 16: "Test circuit for inductive load switching and diode recovery times")	-	155		ns
Q_{rr}	Reverse recovery charge		-	956		nC
I_{RRM}	Reverse recovery current		-	12.5		A
t_{rr}	Reverse recovery time	$I_{SD} = 18\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$, $V_{DD} = 60\text{ V}$, $T_J = 150\text{ °C}$ (see Figure 16: "Test circuit for inductive load switching and diode recovery times")	-	200		ns
Q_{rr}	Reverse recovery charge		-	1450		nC
I_{RRM}	Reverse recovery current		-	13		A

Notes:

⁽¹⁾The value is limited by package.

⁽²⁾Pulse width limited by safe operating area

⁽³⁾ Pulsed: pulse duration = 300 μs , duty cycle 1.5%

2.1 Electrical characteristics (curves)

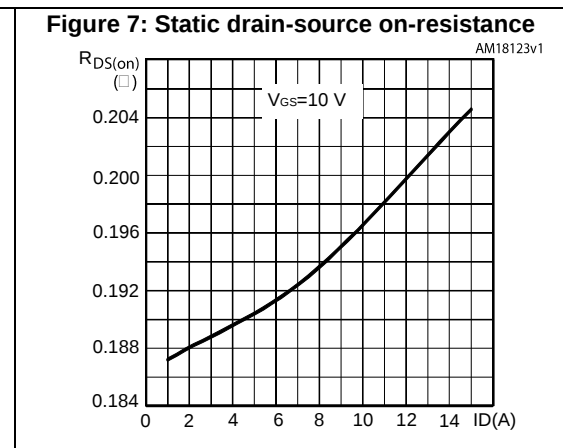
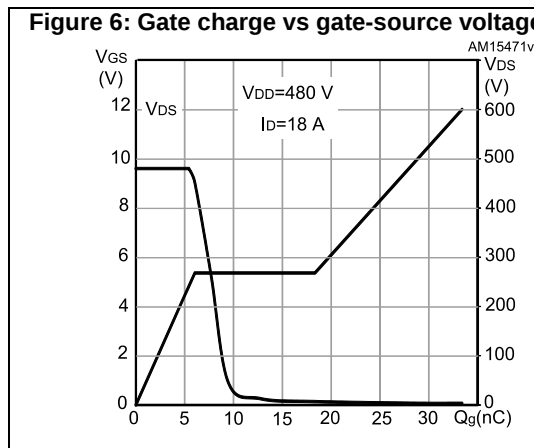
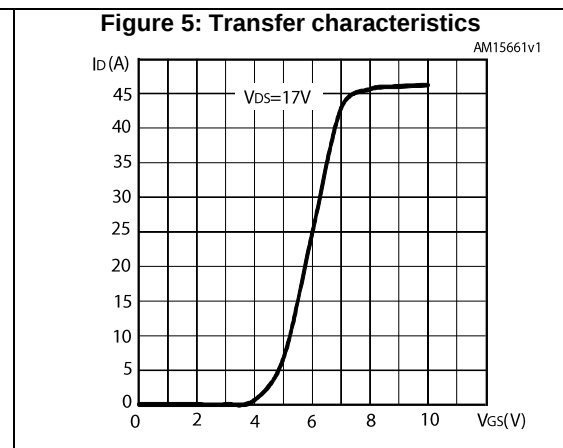
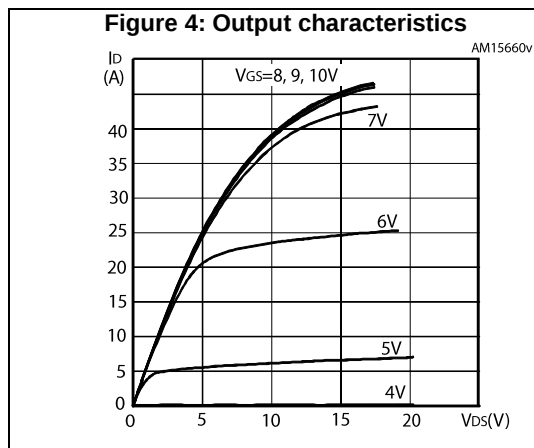
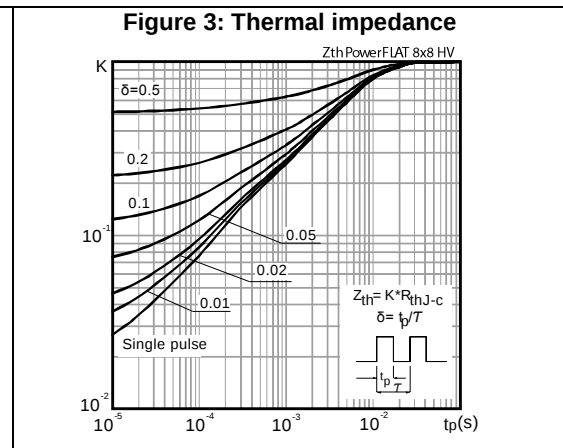
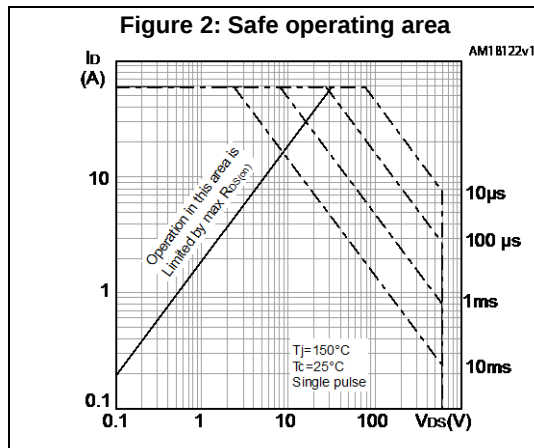


Figure 8: Capacitance variations

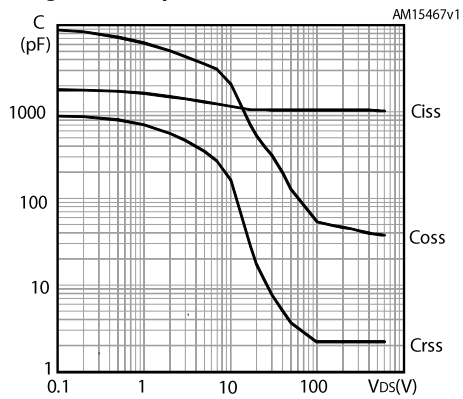


Figure 9: Normalized gate threshold voltage vs temperature

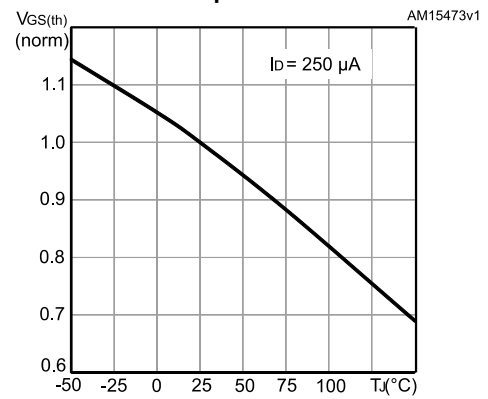


Figure 10: Normalized on-resistance vs temperature

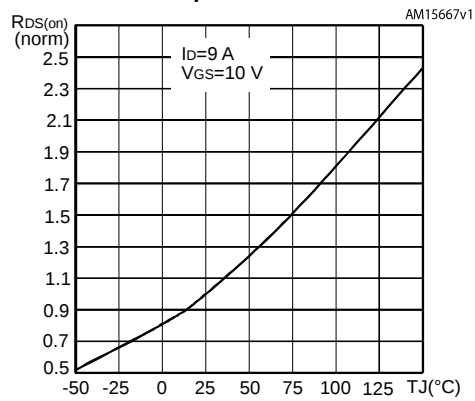


Figure 11: Normalized V(BR)DSS vs temperature

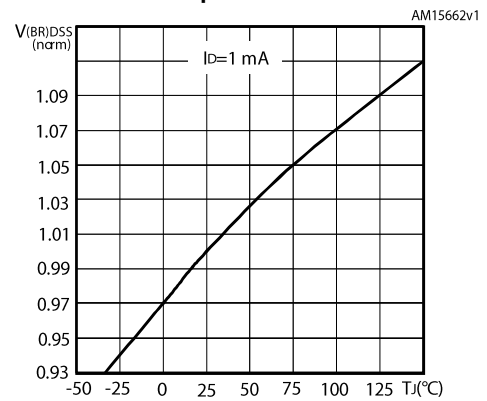


Figure 12: Output capacitance stored energy

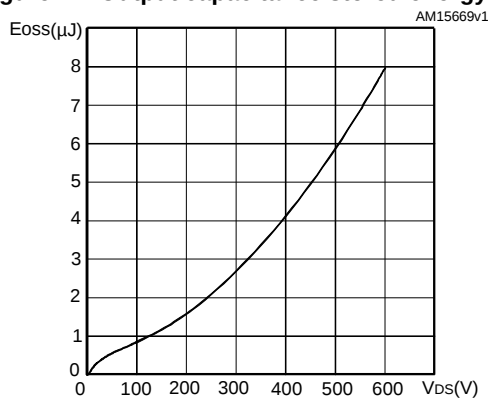
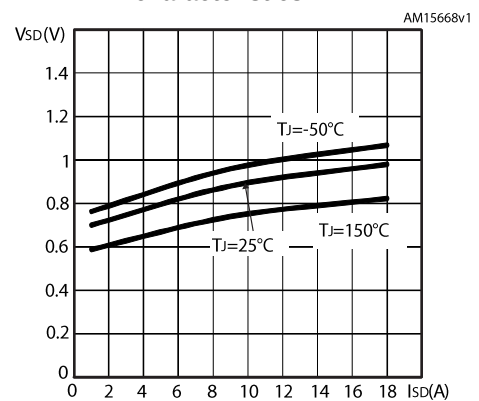


Figure 13: Source-drain diode forward characteristics



3 Test circuits

Figure 14: Switching times test circuit for resistive load



Figure 15: Gate charge test circuit



Figure 16: Test circuit for inductive load switching and diode recovery times



Figure 17: Unclamped inductive load test circuit



Figure 18: Unclamped inductive waveform



Figure 19: Switching time waveform



4 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: **www.st.com**. ECOPACK® is an ST trademark.

4.1 PowerFLAT8x8 HV package information

Figure 20: PowerFLAT™ 8x8 HV package outline

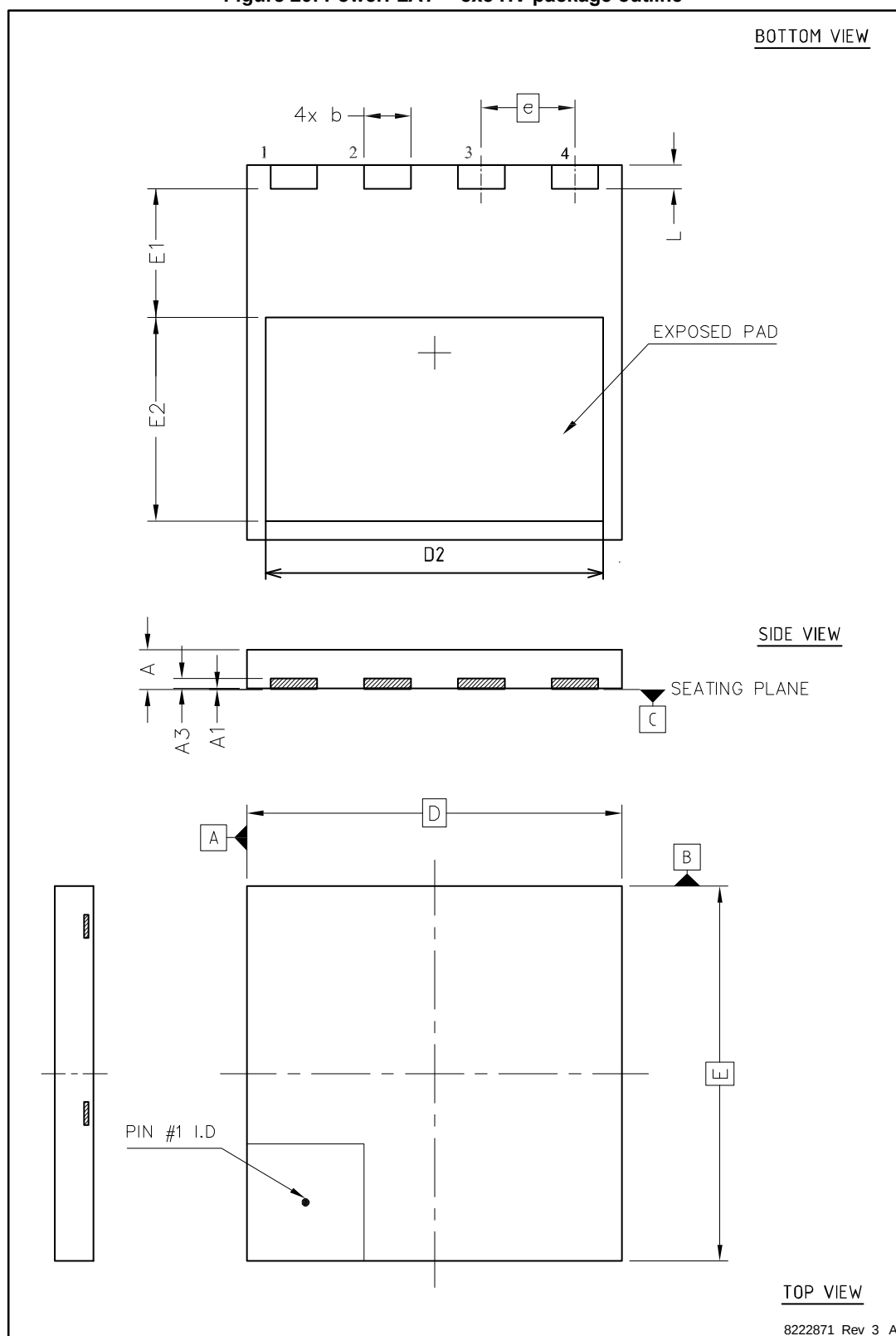
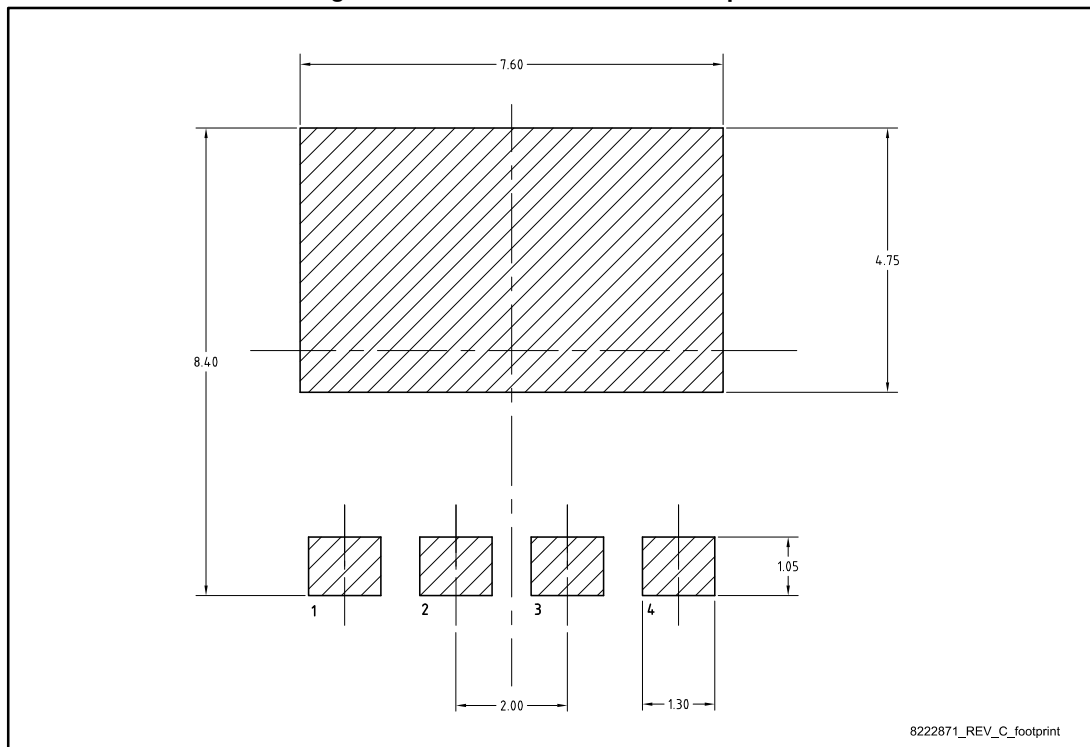


Table 9: PowerFLAT™ 8x8 HV mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	0.75	0.85	0.95
A1	0.00		0.05
A3	0.10	0.20	0.30
b	0.90	1.00	1.10
D	7.90	8.00	8.10
E	7.90	8.00	8.10
D2	7.10	7.20	7.30
E1	2.65	2.75	2.85
E2	4.25	4.35	4.45
e		2.00	
L	0.40	0.50	0.60

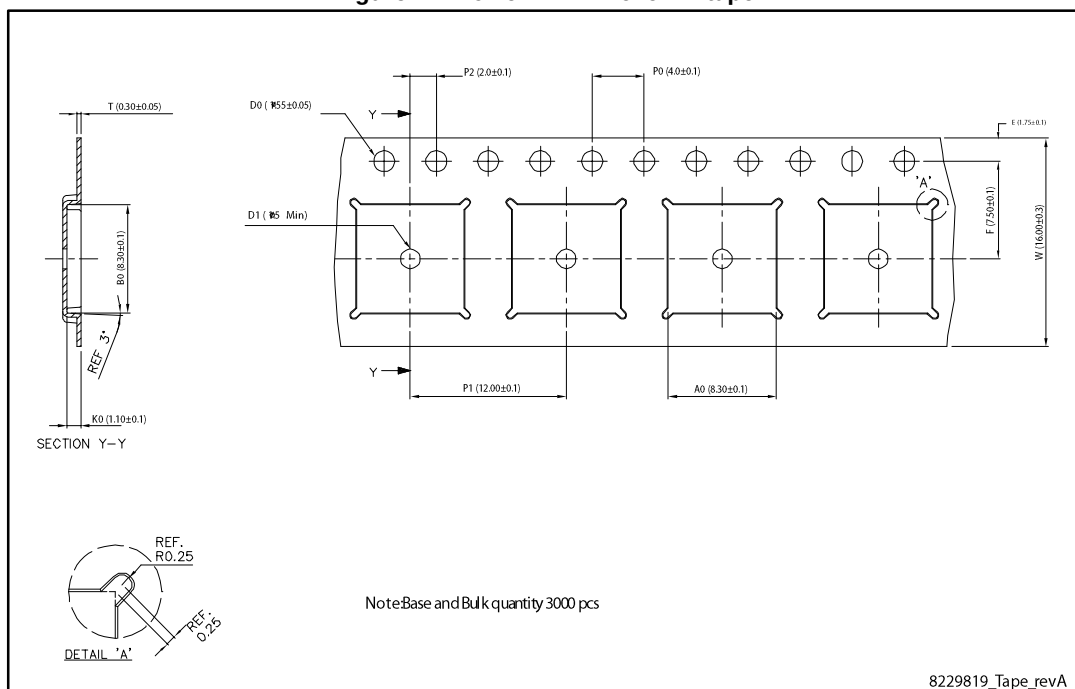
Figure 21: PowerFLAT™ 8x8 HV footprint



All dimensions are in millimeters.

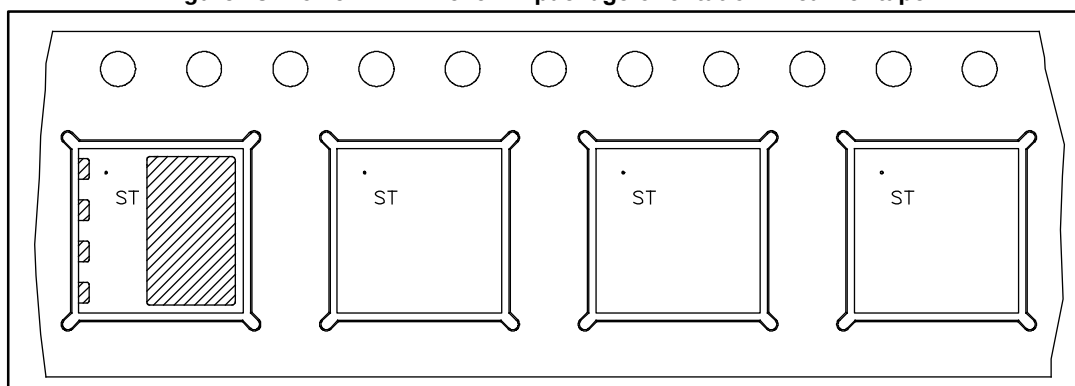
4.2 PowerFLAT8x8 HV packaging information

Figure 22: PowerFLAT™ 8x8 HV tape



All dimensions are in millimeters.

Figure 23: PowerFLAT™ 8x8 HV package orientation in carrier tape





All dimensions are in millimeters.

5 Revision history

Table 10: Document revision history

Date	Revision	Changes
03-Mar-2014	1	First release.
21-Jan-2016	2	Modified: title, features, description and internal schematic in cover page Modified: <i>Section 3: "Test circuits"</i> Updated: <i>Section 4: "Package information"</i> Minor text changes
25-Jul-2016	3	Document status promoted from preliminary to production data.

IMPORTANT NOTICE – PLEASE READ CAREFULLY

STMicroelectronics NV and its subsidiaries ("ST") reserve the right to make changes, corrections, enhancements, modifications, and improvements to ST products and/or to this document at any time without notice. Purchasers should obtain the latest relevant information on ST products before placing orders. ST products are sold pursuant to ST's terms and conditions of sale in place at the time of order acknowledgement.

Purchasers are solely responsible for the choice, selection, and use of ST products and ST assumes no liability for application assistance or the design of Purchasers' products.

No license, express or implied, to any intellectual property right is granted by ST herein.

Resale of ST products with provisions different from the information set forth herein shall void any warranty granted by ST for such product.

ST and the ST logo are trademarks of ST. All other product or service names are the property of their respective owners.

Information in this document supersedes and replaces information previously supplied in any prior versions of this document.

© 2016 STMicroelectronics – All rights reserved

Данный компонент на территории Российской Федерации

Вы можете приобрести в компании MosChip.

Для оперативного оформления запроса Вам необходимо перейти по данной ссылке:

<http://moschip.ru/get-element>

Вы можете разместить у нас заказ для любого Вашего проекта, будь то серийное производство или разработка единичного прибора.

В нашем ассортименте представлены ведущие мировые производители активных и пассивных электронных компонентов.

Нашей специализацией является поставка электронной компонентной базы двойного назначения, продукции таких производителей как XILINX, Intel (ex.ALTERA), Vicor, Microchip, Texas Instruments, Analog Devices, Mini-Circuits, Amphenol, Glenair.

Сотрудничество с глобальными дистрибьюторами электронных компонентов, предоставляет возможность заказывать и получать с международных складов практически любой перечень компонентов в оптимальные для Вас сроки.

На всех этапах разработки и производства наши партнеры могут получить квалифицированную поддержку опытных инженеров.

Система менеджмента качества компании отвечает требованиям в соответствии с ГОСТ Р ИСО 9001, ГОСТ РВ 0015-002 и ЭС РД 009

Офис по работе с юридическими лицами:

105318, г.Москва, ул.Щербаковская д.3, офис 1107, 1118, ДЦ «Щербаковский»

Телефон: +7 495 668-12-70 (многоканальный)

Факс: +7 495 668-12-70 (доб.304)

E-mail: info@moschip.ru

Skype отдела продаж:

moschip.ru

moschip.ru_4

moschip.ru_6

moschip.ru_9